

1. General description

Silicon Carbide MOSFET in a 3-lead TO247 plastic package, designed for high frequency, high efficiency systems.



2. Features and benefits

- Low on-resistance
- Fast switching speed
- 0V turn-off gate voltage for simple gate drive
- 100% UIS Tested
- Easy to parallel
- Controllable dV/dt for optimized EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Switch Mode Power Supplies
- UPS
- Solar string inverter and solar optimizer
- EV Charger
- Motor Drives

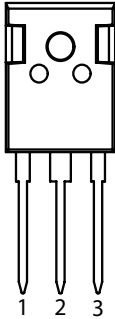
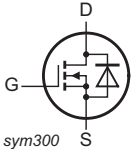
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Absolute maximum rating							
V _{DS}	drain-source voltage	25 °C ≤ T _J ≤ 175 °C		-	-	1200	V
I _D	drain current	V _{GS} = 20 V; T _{mb} = 25 °C		-	-	24	A
P _{tot}	total power dissipation	T _{mb} = 25 °C		-	-	155	W
T _J	junction temperature			-55	-	175	°C
Static characteristics							
R _{DS(on)}	drain-source on-state resistance	V _{GS} = 20 V; I _D = 10 A; T _J = 25 °C		-	160	196	mΩ
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 800 V; V _{GS} = 0V/20 V; T _J = 25 °C		-	35	-	nC
Q _{GD}	gate-drain charge			-	8	-	nC
Source-drain diode							
Q _r	recovered charge	I _{SD} = 10 A; di/dt = 500 A/μs; V _{DS} = 400 V; T _J = 25 °C		-	78	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSCM160120W	TO247	WNSCM160120WQ	Tube	30	SOT429	25-Mar-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes
WNSCM160120W	WNSCM 160120W

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_J \leq 175\text{ °C}$		-	1200	V
$V_{GS,max}$	gate-source voltage			-10	25	V
$V_{GS,op}$	gate-source voltage			-5	20	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$		-	155	W
I_D	drain current	$V_{GS} = 20\text{ V}; T_{mb} = 25\text{ °C}$		-	24	A
		$V_{GS} = 20\text{ V}; T_{mb} = 100\text{ °C}$		-	17	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}; T_{mb} = 25\text{ °C}$		-	34	A
E_{as}	single pulse drain-to-source avalanche	$I_{AS} = 13\text{ A}; L = 1\text{ mH}; V_{DD} = 100\text{ V}, T_{J(init)} = 25\text{ °C}$		85	-	mJ
T_{stg}	storage temperature			-55	175	°C
T_J	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C

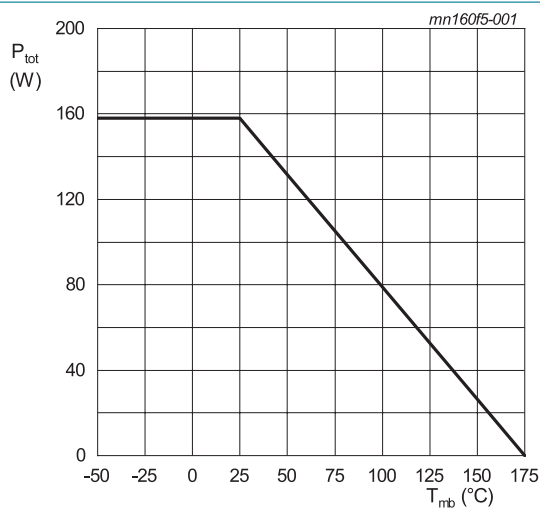


Fig. 1. Normalized total power dissipation as a function of mounting base temperature; maximum values

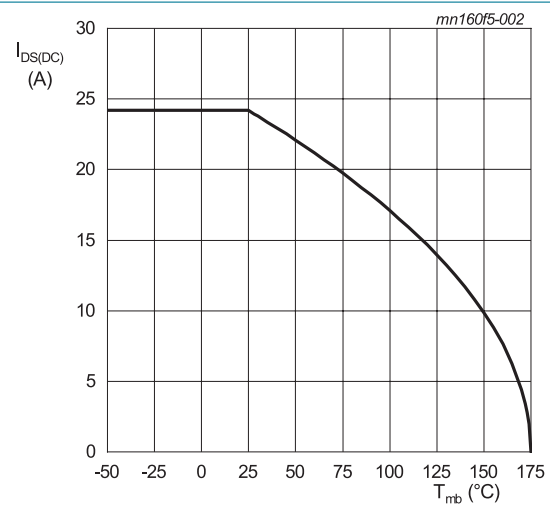


Fig. 2. Continuous Drain Current as a function of mounting base temperature

9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	40	-	K/W
M_d	Mounting torque	M3 or 6 - 32 screw	-	-	0.6	Nm

Note: It is recommended that a metal washer is inserted between screw head and mounting tab.
Do not use self-tapping screws.
Device is ESD sensitive. Handling precautions are recommended.

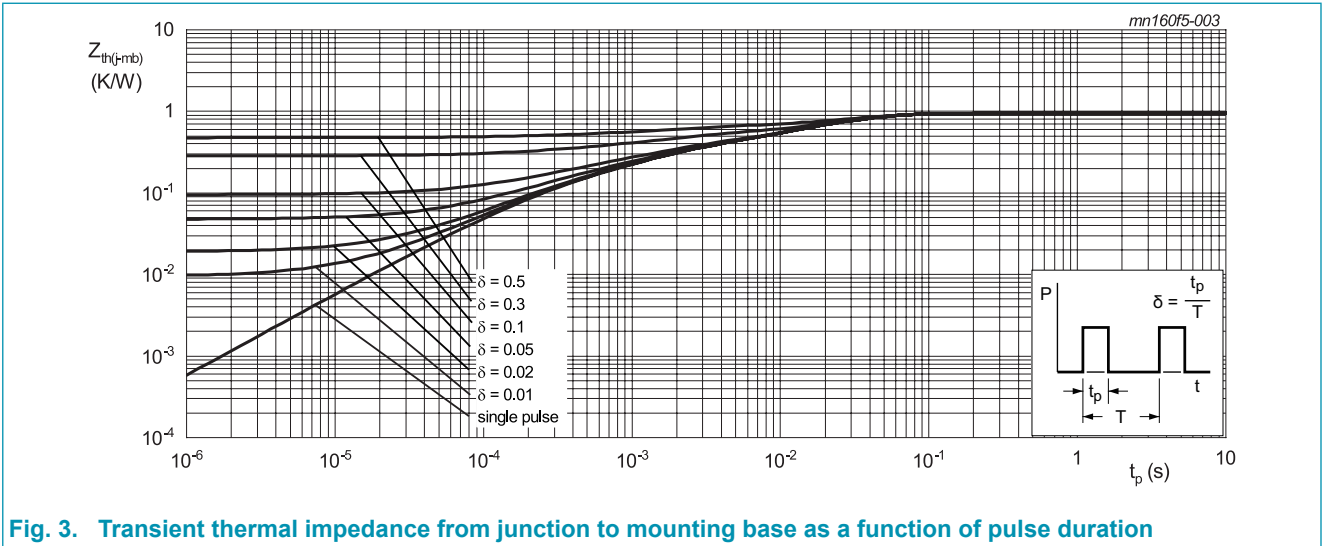
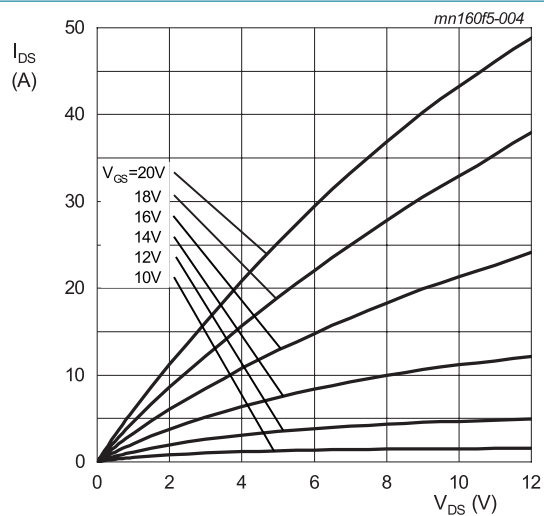


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

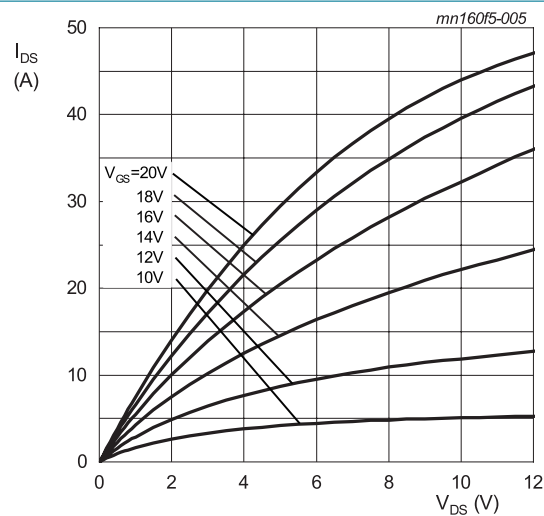
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit	
Static characteristics								
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 100 μA; V _{GS} = 0 V; T _J = 25 °C		1200	-	-	V	
V _{GS(th)}	gate-source threshold voltage	I _D = 3 mA; V _{DS} = 10 V; T _J = 25 °C		2.5	3.5	4.5	V	
		I _D = 3 mA; V _{DS} = 10 V; T _J = 150 °C		-	2.5	-	V	
I _{DSS}	drain leakage current	V _{DS} = 1200 V; V _{GS} = 0 V; T _J = 25 °C		-	0.1	100	μA	
		V _{DS} = 1200 V; V _{GS} = 0 V; T _J = 150 °C		-	1	-	μA	
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _J = 25 °C		-	10	100	nA	
		V _{GS} = -10 V; V _{DS} = 0 V; T _J = 25 °C		-	10	100	nA	
R _{DS(on)}	drain-source on-state resistance	V _{GS} = 20 V; I _D = 10 A; T _J = 25 °C		-	160	196	mΩ	
		V _{GS} = 20 V; I _D = 10 A; T _J = 150 °C		-	220	-	mΩ	
R _G	gate resistance	f = 1 MHz; T _J = 25 °C		-	3.9	-	Ω	
g _{fs}	transconductance	V _{DS} = 20 V; I _D = 10 A; T _J = 25 °C		-	4.5	-	S	
Dynamic characteristics								
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 800 V; V _{GS} = 0 V/20 V; T _J = 25 °C		-	35	-	nC	
Q _{GS}	gate-source charge			-	12	-	nC	
Q _{GD}	gate-drain charge			-	8	-	nC	
C _{iss}	input capacitance	V _{DS} = 1000 V; V _{GS} = 0 V; f = 1 MHz; T _J = 25 °C		-	736	-	pF	
C _{oss}	output capacitance			-	40	-	pF	
C _{rss}	reverse transfer capacitance			-	3.8	-	pF	
E _{oss}	Coss stored energy			-	20	-	μJ	
t _{d(on)}	turn-on delay time		V _{DS} = 800 V; V _{GS} = -5/20 V; R _{G(ext)} = 0 Ω; I _D = 10 A; L = 360 μH; T _J = 25 °C		-	6	-	ns
t _r	rise time				-	21	-	ns
t _{d(off)}	turn-off delay time				-	12	-	ns
t _f	fall time			-	41	-	ns	
E _{on}	turn-on energy (SiC Diode FWD)			-	192	-	μJ	
E _{off}	turn-off energy (SiC Diode FWD)			-	5	-	μJ	
E _{on}	turn-on energy (Body Diode FWD)			-	307	-	μJ	
E _{off}	turn-off energy (Body Diode FWD)		-	10	-	μJ		
Source-drain diode								
V _{SD}	source-drain voltage	V _{GS} = 0 V; I _F = 5 A; T _J = 25 °C		-	4.1	-	V	
		V _{GS} = 0 V; I _F = 5 A; T _J = 150 °C		-	3.5	-	V	
t _{rr}	reverse recovery time	I _{SD} = 10 A; di/dt = 500 A/μs; V _{DS} = 400 V; T _J = 25 °C		-	38	-	ns	
Q _r	recovered charge			-	78	-	nC	
I _{rrm}	reverse recovery current			-	3.5	-	A	



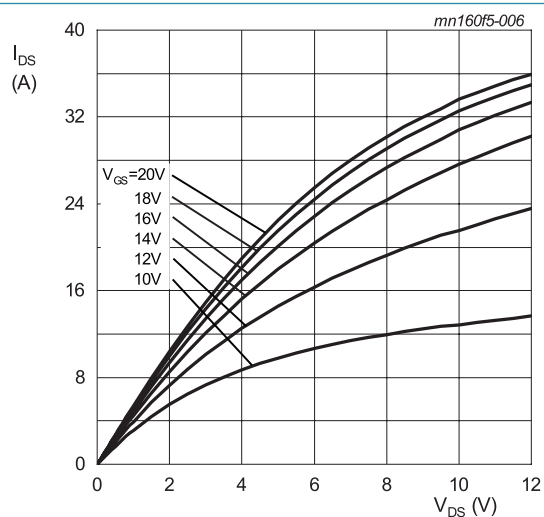
$T_j = -55\text{ }^{\circ}\text{C}$; $t_p < 200\text{ }\mu\text{s}$

Fig. 4. Output characteristics; drain current as a function of drain-source voltage; typical values



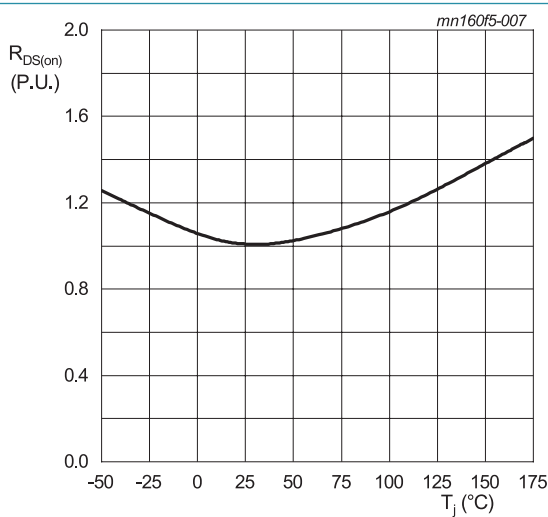
$T_j = 25\text{ }^{\circ}\text{C}$; $t_p < 200\text{ }\mu\text{s}$

Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values



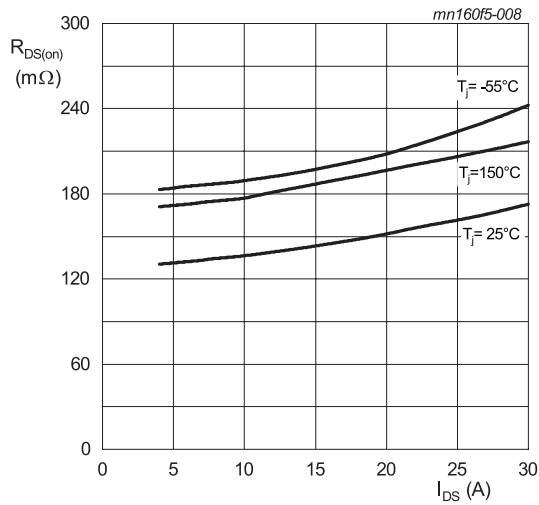
$T_j = 150\text{ }^{\circ}\text{C}$; $t_p < 200\text{ }\mu\text{s}$

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values



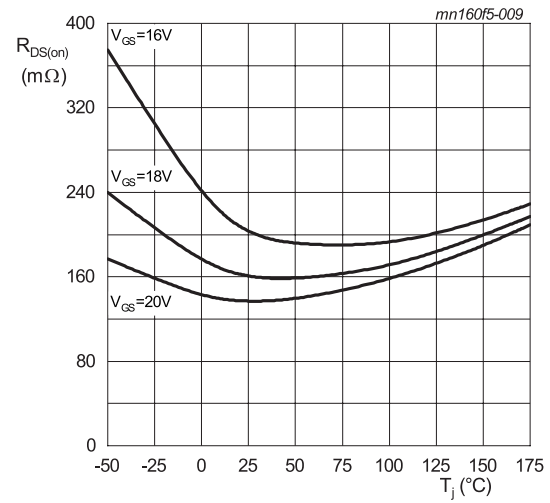
$I_{DS} = 20\text{ A}$; $V_{GS} = 20\text{ V}$; $t_p < 200\text{ }\mu\text{s}$

Fig. 7. Normalized drain-source on-state resistance as a function of junction temperature



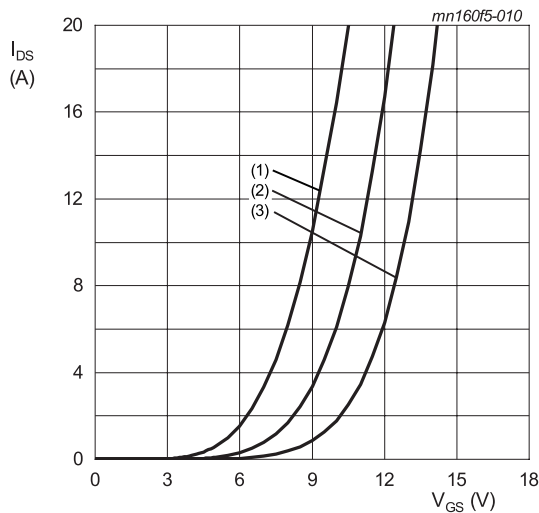
$V_{GS} = 20\text{ V}$; $t_p < 200\text{ }\mu\text{s}$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



$I_{DS} = 10\text{ A}$; $t_p < 200\text{ }\mu\text{s}$

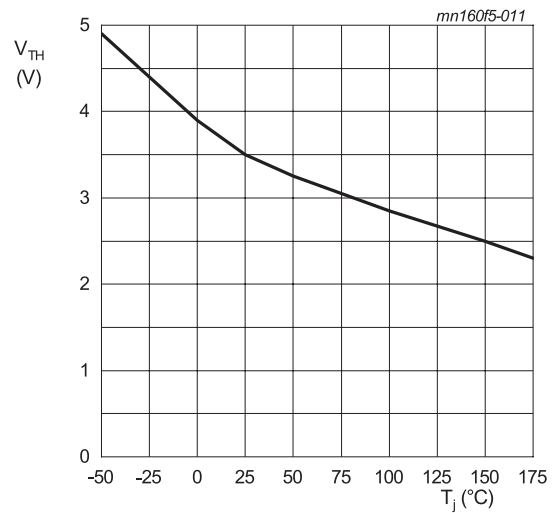
Fig. 9. Drain-source on-state resistance as a function of junction temperature



$V_{DS} = 20\text{ V}$; $t_p < 200\text{ }\mu\text{s}$

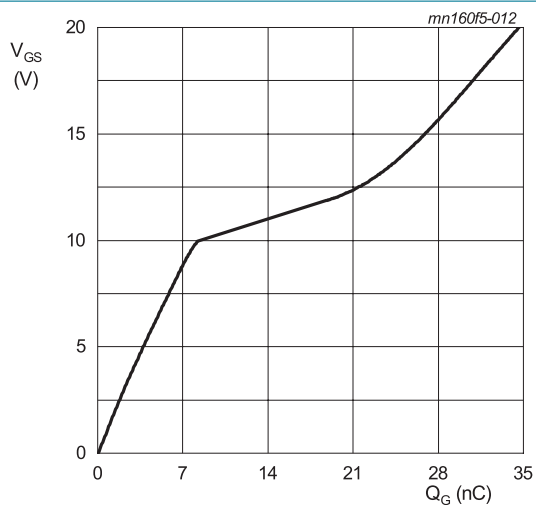
- (1) $T_J = 150^\circ\text{C}$
- (2) $T_J = 25^\circ\text{C}$
- (3) $T_J = -55^\circ\text{C}$

Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values



$V_{DS} = 20\text{ V}$; $I_{DS} = 3\text{ mA}$

Fig. 11. Threshold voltage as a function of junction temperature



$I_{DS} = 10 \text{ A}$; $I_{GS} = 1 \text{ mA}$; $V_{DS} = 800 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$

Fig. 12. Gate-source voltage as a function of gate charge; typical values

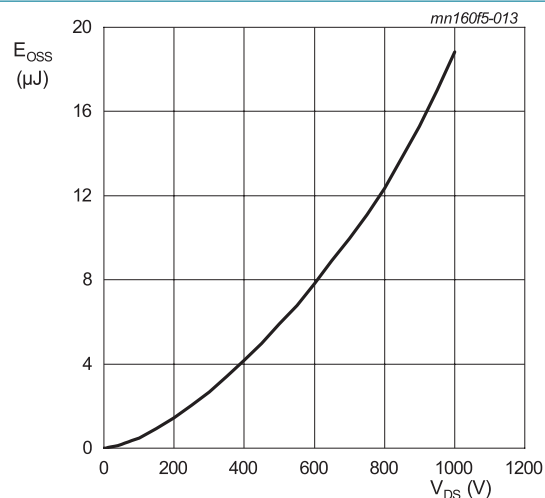
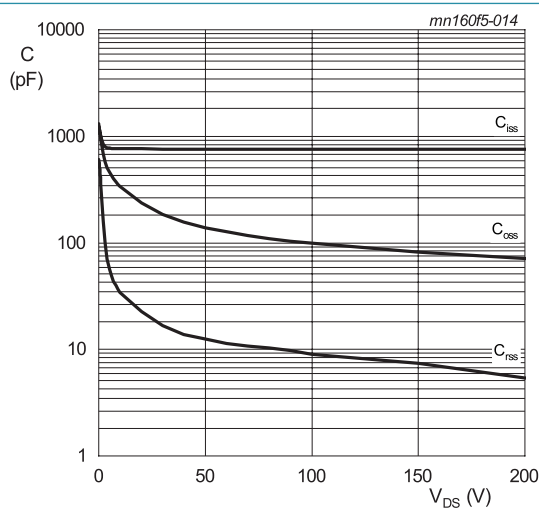
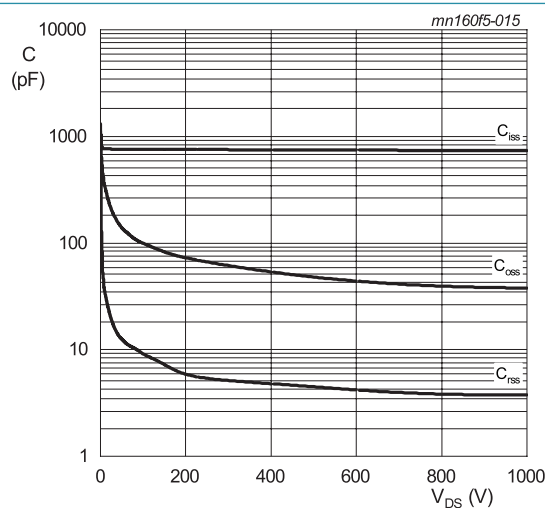


Fig. 13. Output capacitor stored energy as a function of drain-source voltage



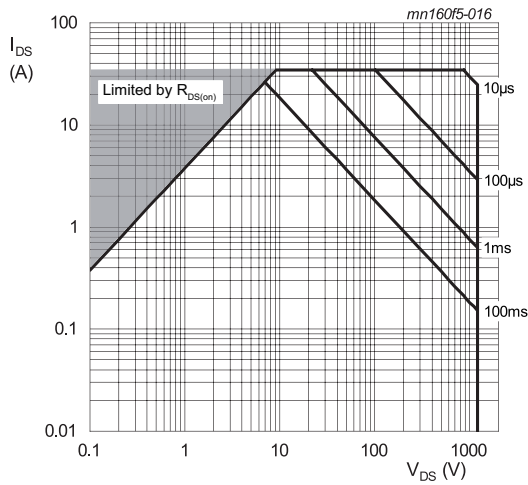
$V_{DS} = 0 - 200 \text{ V}$
 $T_j = 25 \text{ }^\circ\text{C}$; $V_{AC} = 25 \text{ mV}$; $f = 1 \text{ MHz}$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{DS} = 0 - 1000 \text{ V}$
 $T_j = 25 \text{ }^\circ\text{C}$; $V_{AC} = 25 \text{ mV}$; $f = 1 \text{ MHz}$

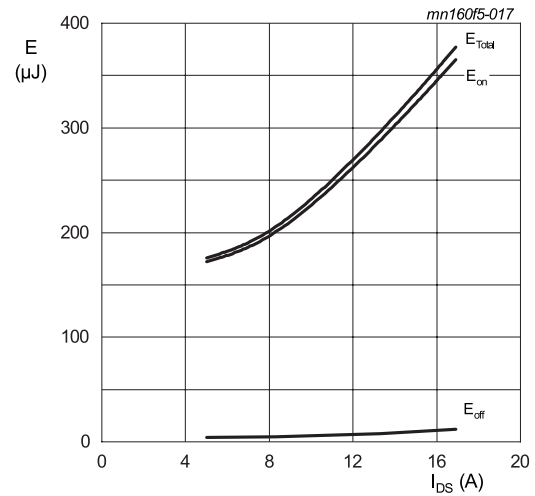
Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$T_c = 25\text{ }^{\circ}\text{C}$; $D = 0$

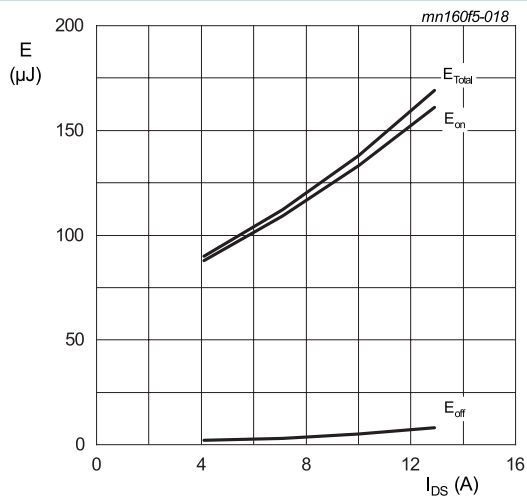
Parameter: t_p

Fig. 16. Forward bias safe operating area



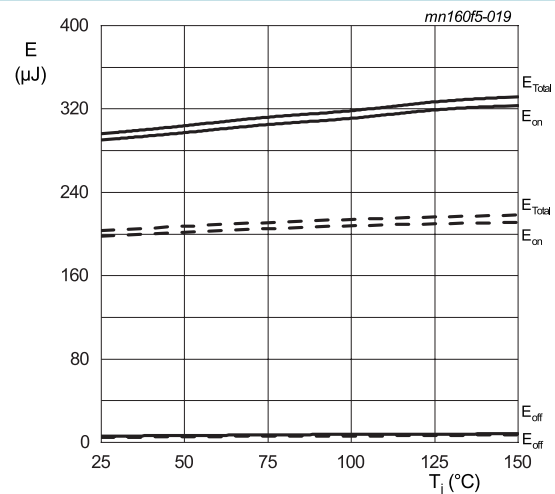
$T_j = 25\text{ }^{\circ}\text{C}$; $V_{DD} = 800\text{ V}$; $R_{G(ext)} = 0\text{ }\Omega$; $V_{GS} = -5\text{V}/20\text{ V}$
FWD = WN5C051200; $L = 360\text{ }\mu\text{H}$

Fig. 17. Clamped Inductive Switching Energy as a function of drain current



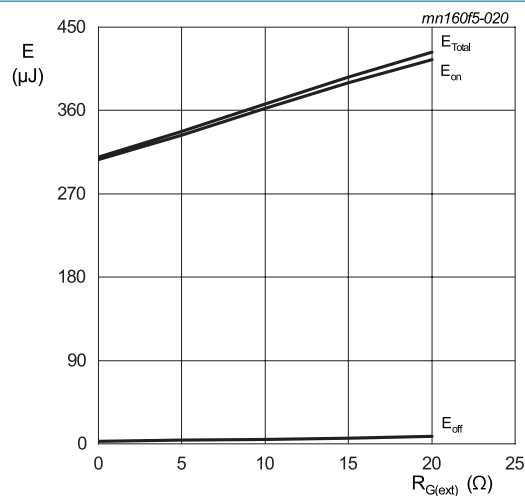
$T_j = 25\text{ }^{\circ}\text{C}$; $V_{DD} = 600\text{ V}$; $R_{G(ext)} = 0\text{ }\Omega$; $V_{GS} = -5\text{V}/20\text{ V}$
FWD = WN5C051200; $L = 360\text{ }\mu\text{H}$

Fig. 18. Clamped Inductive Switching Energy as a function of drain current



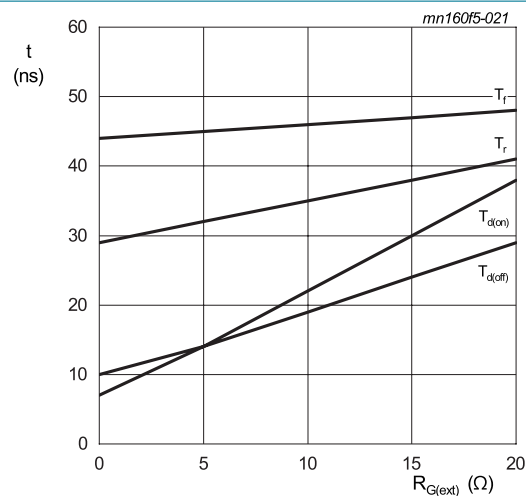
$I_{DS} = 10\text{ A}$; $V_{DD} = 800\text{ V}$; $R_{G(ext)} = 0\text{ }\Omega$; $V_{GS} = -5\text{V}/20\text{ V}$
 $L = 360\text{ }\mu\text{H}$
FWD = WN5C051200
FWD = WN5C051200(- -)

Fig. 19. Clamped Inductive Switching Energy as a function of junction temperature



T_j = 25 °C; V_{DD} = 800 V; I_{DS} = 10 A; V_{GS} = -5V/20 V
FWD = WNSCM160120W; L = 360 μH

Fig. 20. Clamped Inductive Switching Energy as a function of external gate resistance



T_j = 25 °C; V_{DD} = 800 V; I_{DS} = 10 A; V_{GS} = -5V/20 V
FWD = WNSCM160120W; L = 360 μH

Fig. 21. Switching time as a function of external gate resistance

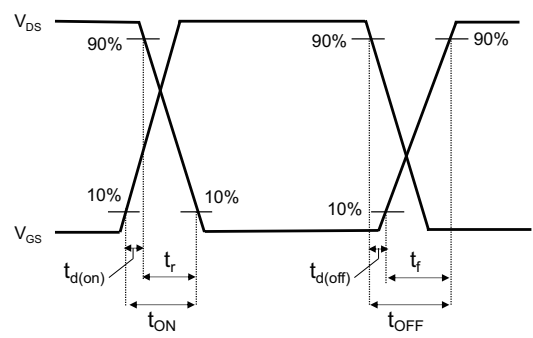
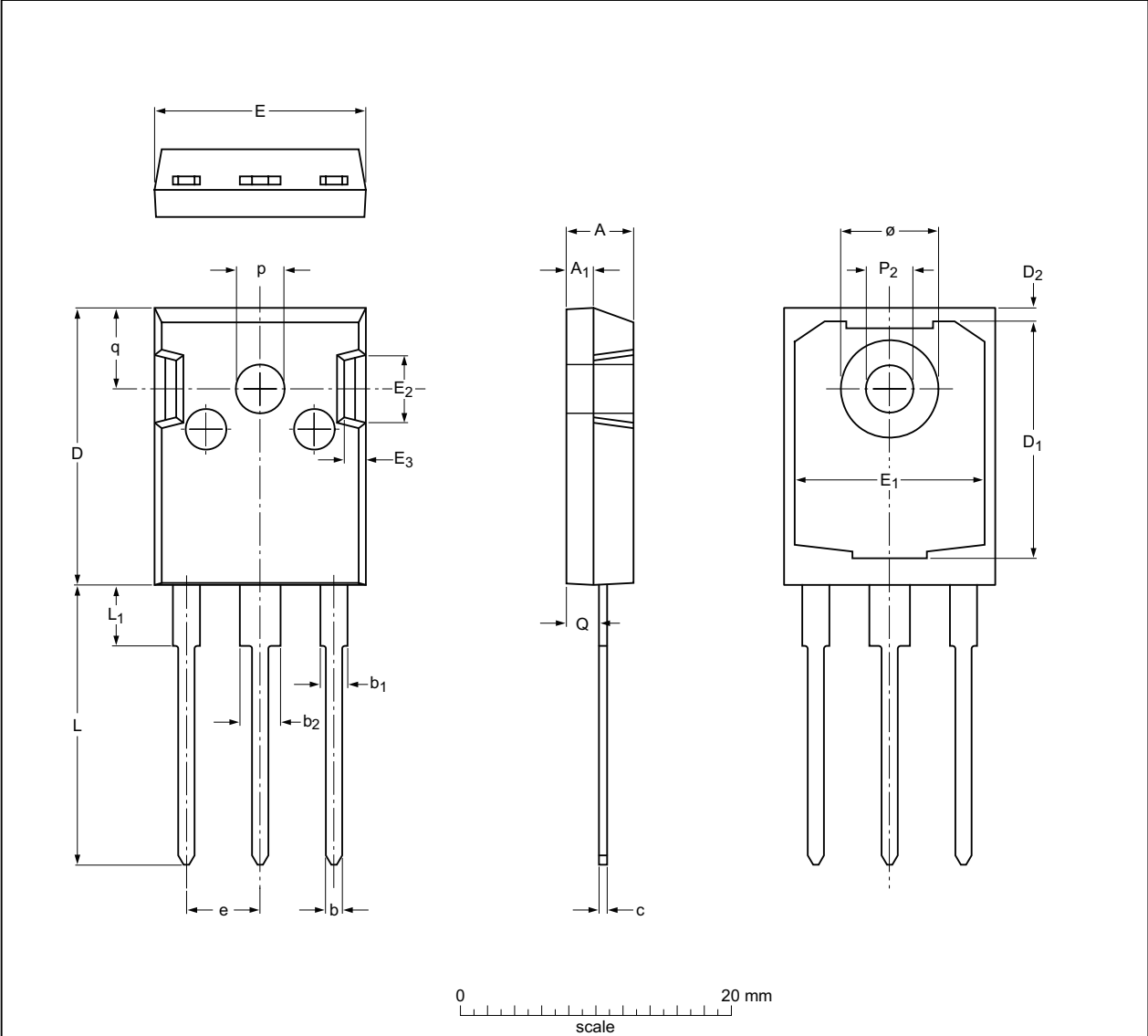


Fig. 22. Switching time definition

11. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247 SOT429



Dimensions (mm are the original dimensions)

Unit ⁽¹⁾	A	A ₁	b	b ₁	b ₂	c	D	D ₁	D ₂	E	E ₁	E ₂	E ₃	e ⁽¹⁾	L	L ₁	P ₂	p	Q	q	ø
max	5.20	2.10	1.40	2.20	3.20	0.70	20.6	17.68	1.20	15.75	14.22	5.20	1.80	5.45	20.90	4.75	3.60	3.70	2.60	6.18	7.30
nom																					
min	4.70	1.90	1.00	1.80	2.80	0.50	20.3	17.28	0.80	15.45	13.82	4.80	1.40		20.40	4.25	3.40	3.50	2.20	5.78	7.10

Note
1. Basic spacing between centers.

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT429	TO-247					04-09-14 13-03-25

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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13. Contents

1. General description.....	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data.....	1
5. Pinning information.....	2
6. Ordering information.....	2
7. Ordering information.....	2
8. Limiting values	3
9. Thermal & Mechanical characteristics	4
10. Characteristics.....	5
11. Package outline	11
12. Legal information	12
13. Contents	14

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For sales office addresses, please send an email to: salesaddresses@ween-semi.com

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